

# P-Channel 20 V (D-S) MOSFET

| PRODUCT SUMMARY     |  |                    |                       |  |  |  |
|---------------------|--|--------------------|-----------------------|--|--|--|
| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (mΩ)(Typ.)           | I <sub>D</sub> (A) | Q <sub>g</sub> (Typ.) |  |  |  |
| - 20                | 6.6 at V <sub>GS</sub> = - 4.5 V         | - 42               | 63 nC                 |  |  |  |
| - 20                | $8.9 \text{ at V}_{GS} = -2.5 \text{ V}$ | - 42               |                       |  |  |  |

#### **FEATURES**

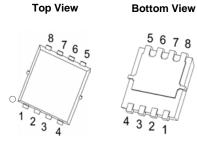
- DT-Trench Power MOSFET
- Low R<sub>DS(ON)</sub>×FOM
- · Extremely low switching loss

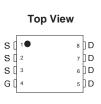


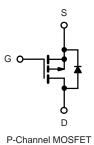
#### **APPLICATIONS**

- Load switch
- Battery protection

#### PDFN3.3\*3.3-8L Pin Configuration







| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted) |                         |                                   |             |    |  |  |
|--|-------------------------|-----------------------------------|-------------|----|--|--|
| PARAMETER  | SYMBOL                  | LIMIT                             | UNIT        |    |  |  |
| Drain-Source Voltage   | V <sub>DS</sub>         | - 20                              | V           |    |  |  |
| Gate-Source Voltage  | $V_{GS}$                | ± 12                              |             |    |  |  |
| Ocation of Ducie Comment /T 150 %O/2   | T <sub>C</sub> = 25 °C  | 1                                 | - 42        | А  |  |  |
| Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>                  | T <sub>C</sub> = 100 °C | — I <sub>D</sub>                  | - 30        |    |  |  |
| Pulsed Drain Current <sup>b</sup>  | I <sub>DM</sub>         | - 168                             |             |    |  |  |
| Single Avalanche Energy  | E <sub>AS</sub>         | 305                               | mJ          |    |  |  |
| Maximum Dower Dissipations   | T <sub>C</sub> = 25 °C  | D                                 | 78          | W  |  |  |
| Maximum Power Dissipation <sup>c</sup>   | T <sub>C</sub> = 100 °C | P <sub>D</sub>                    | 31.2        | ]  |  |  |
| Operating Junction and Storage Temperature Range                                 |                         | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 | °C |  |  |

| THERMAL RESISTANCE RATINGS                   |                   |       |      |  |  |
|--|-------------------|-------|------|--|--|
| PARAMETER                                    | SYMBOL            | LIMIT | UNIT |  |  |
| Junction-to-Ambient (PCB Mount) <sup>d</sup> | R <sub>thJA</sub> | 62    | °C/W |  |  |
| Junction-to-Case (Drain)                     | R <sub>thJC</sub> | 1.6   |      |  |  |

#### Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



| PARAMETER                                     | SYMBOL              | TEST CONDITIONS   | MAINI | TYP. | MAN   | LINUT |  |
|---|---------------------|---|-------|------|-------|-------|--|
|   | SYMBOL              | TEST CONDITIONS   | MIN.  | ITP. | MAX.  | UNIT  |  |
| Static  |                     |   |       | ı    |       |       |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$                          | - 20  | -    | -     | V     |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$                                   |       | -    | - 1   |       |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$                       | -     | -    | ± 100 | nA    |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | $V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$                          | -     | -    | - 1   | μΑ    |  |
|   |                     | $V_{GS} = -4.5 \text{ V}, I_D = -8 \text{ A}$                           | -     | 6.6  | 7.9   | mΩ    |  |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub> | $V_{GS} = -2.5 \text{ V}, I_D = -8 \text{ A}$                           | -     | 8.9  | 11    |       |  |
|   |                     | V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 8 A                       | -     | 13.2 | 17    |       |  |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 10 A                        |       | 70   |       | S     |  |
| Dynamic <sup>b</sup>                          |                     |   |       |      |       |       |  |
| Input Capacitance                             | C <sub>iss</sub>    |   | -     | 4550 | -     | pF    |  |
| Output Capacitance                            | C <sub>oss</sub>    | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 10 V, f = 100 MHz            | -     | 586  | -     |       |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    |   | -     | 543  | -     |       |  |
| Total Gate Charge c                           | Qg                  |   | -     | 63   | -     | nC    |  |
| Gate-Source Charge c                          | $Q_{gs}$            | $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -8 \text{ A}$ | -     | 10   | -     |       |  |
| Gate-Drain Charge <sup>c</sup>                | $Q_{gd}$            |   | -     | 15   | -     |       |  |
| Gate Resistance                               | Rq                  | f = 1 MHz   | -     | 4.5  | -     | Ω     |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |   | -     | 18   | -     |       |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 8 A,                       | -     | 52   | -     | ns    |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> | $V_{GS} = -4.5 \text{ V}, R_{g} = 0.5 \Omega$                           | -     | 95   | -     |       |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      |   | -     | 40   | -     |       |  |
| Drain-Source Body Diode Ratings ar            | •                   | stics <sup>b</sup> (T <sub>C</sub> = 25 °C)                             |       |      |       |       |  |
| Continuous Source Current                     | I <sub>S</sub>      | T <sub>C</sub> = 25 °C  | -     | -    | - 42  | Α     |  |
| Pulsed Current                                | I <sub>SM</sub>     |   | -     | -    | - 168 | Α     |  |
| Forward Voltage <sup>a</sup>                  | $V_{SD}$            | I <sub>S</sub> = -8 A, V <sub>GS</sub> = 0 V                            | -     | -    | - 1.2 | V     |  |
| Reverse Recovery Time                         | t <sub>rr</sub>     |   | -     | 60   | -     | ns    |  |
| Reverse Recovery Charge                       | Q <sub>rr</sub>     | l <sub>S</sub> = - 8 A, di/dt = 100 A/μs                                | _     | 55   | -     | nC    |  |

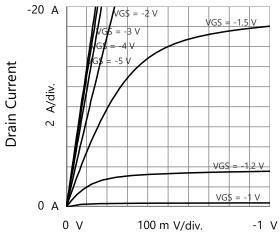
#### Notes

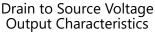
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

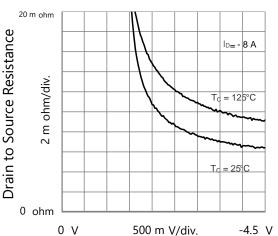
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



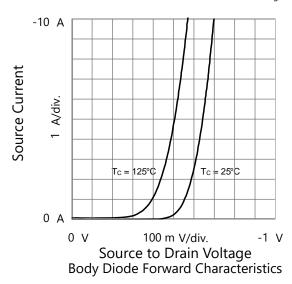
#### TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)

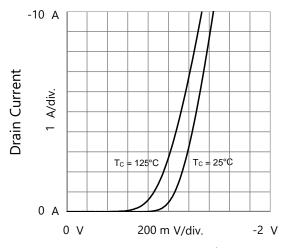




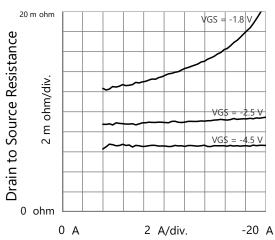


Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

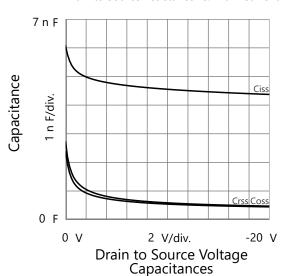




Gate to Source Voltage Transfer Characteristics

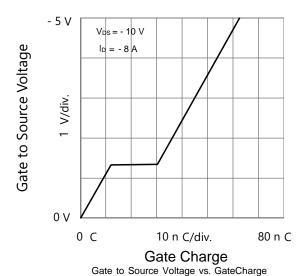


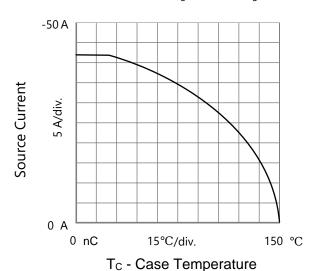
Drain Current
Drain to Source Resistance vs. Drain Current

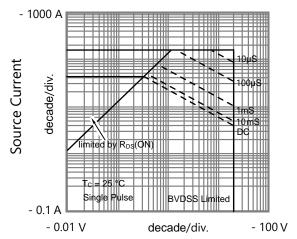




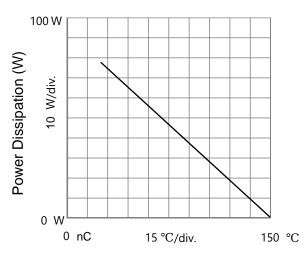
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



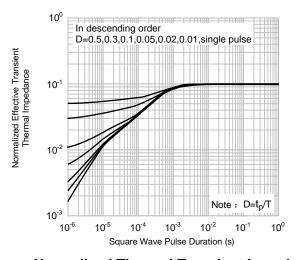




Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



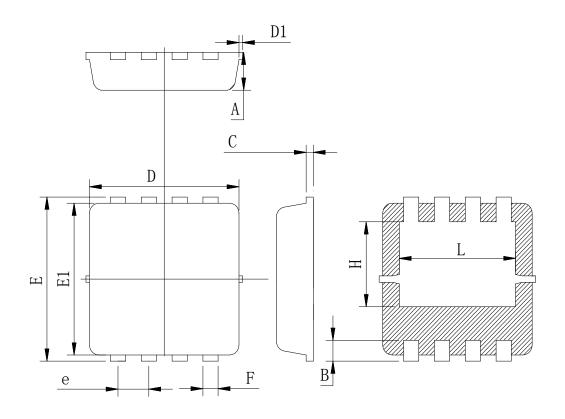
T<sub>C</sub> - Case Temperature



**Normalized Thermal Transient Impedance** 



### **PDFN 3.3X3.3 PACKAGE OUTLINE**



**COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

| Symbol | Min   | Тур   | Max   |
|--------|-------|-------|-------|
| A      | 0.600 | 0.775 | 1.000 |
| В      | 0.20  | 0.38  | 0.55  |
| С      | 0.05  | 0.15  | 0.40  |
| D      | 2.80  | 3.15  | 3.60  |
| D1     | •     | -     | 0.15  |
| Е      | 3.00  | 3.35  | 3.70  |
| E1     | 2.60  | 3.10  | 3.45  |
| e      | 0.50  | 0.65  | 0.80  |
| F      | 0.15  | 0.32  | 0.45  |
| Н      | 1.25  | 1.73  | 2.10  |
| L      | 2.20  | 2.45  | 2.85  |





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